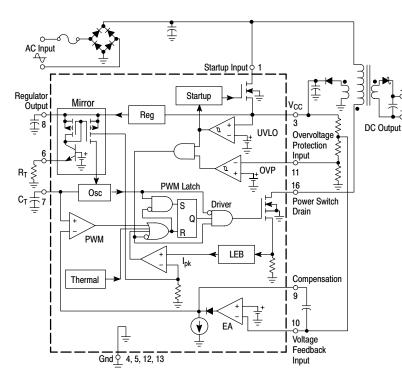
High Voltage Switching Regulator

The MC33362 is a monolithic high voltage switching regulator that is specifically designed to operate from a rectified 120 VAC line source. This integrated circuit features an on-chip 500 V/2.0 A SENSEFET™ power switch, 250 V active off-line startup FET, duty cycle controlled oscillator, current limiting comparator with a programmable threshold and leading edge blanking, latching pulse width modulator for double pulse suppression, high gain error amplifier, and a trimmed internal bandgap reference. Protective features include cycle-by-cycle current limiting, input undervoltage lockout with hysteresis, output overvoltage protection, and thermal shutdown. This device is available in a 16-lead dual-in-line and wide body surface mount packages.

- On-Chip 500 V, 2.0 A SENSEFET Power Switch
- Rectified 120 VAC Line Source Operation
- On-Chip 250 V Active Off-Line Startup FET
- Latching PWM for Double Pulse Suppression
- Cycle–By–Cycle Current Limiting
- Input Undervoltage Lockout with Hysteresis
- Output Overvoltage Protection Comparator
- Trimmed Internal Bandgap Reference
- Internal Thermal Shutdown



This device contains 221 active transistors.

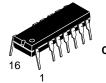
Figure 1. Simplified Application



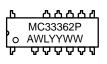
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MARKING DIAGRAMS









SO-16W DW SUFFIX CASE 751N



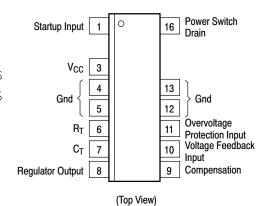
A = Assembly Location

WL = Wafer Lot

YY = Year

WW = Work Week

PIN CONNECTIONS



ORDERING INFORMATION

Device	Package	Shipping
MC33362DW	SO-16W	47 Units/Rail
MC33362DWR2	SO-16W	1000 Tape & Reel
MC33362P	PDIP-16	25 Units/Rail

MAXIMUM RATINGS (Note 1)

Rating	Symbol	Value	Unit
Power Switch (Pin 16) Drain Voltage Drain Current	V _{DS}	500 2.0	V A
Startup Input Voltage (Pin 1, Note 2) Pin 3 = Gnd Pin 3 \leq 1000 μ F to ground	V _{in}	250 400	V
Power Supply Voltage (Pin 3)	V _{CC}	40	V
Input Voltage Range Voltage Feedback Input (Pin 10) Compensation (Pin 9) Overvoltage Protection Input (Pin 11) R _T (Pin 6) C _T (Pin 7)	V _{IR}	-1.0 to V _{reg}	V
Thermal Characteristics P Suffix, Dual–In–Line Case 648E Thermal Resistance, Junction–to–Air Thermal Resistance, Junction–to–Case (Pins 4, 5, 12, 13) DW Suffix, Surface Mount Case 751N Thermal Resistance, Junction–to–Air Thermal Resistance, Junction–to–Case (Pins 4, 5, 12, 13) Refer to Figures 16 and 17 for additional thermal information.	R _{0JA} R _{0JC} R _{0JA} R _{0JC}	80 15 95 15	°C/W
Operating Junction Temperature	T _J	- 25 to +150	°C
Storage Temperature	T _{stg}	- 55 to +150	°C

ELECTRICAL CHARACTERISTICS (V_{CC} = 20 V, R_T = 10 k, C_T = 390 pF, $C_{Pin~8}$ = 1.0 μ F, for typical values T_J = 25°C, for min/max values T_J is the operating junction temperature range that applies (Note 3), unless otherwise noted.)

Characteristic	Symbol	Min	Тур	Max	Unit
REGULATOR (Pin 8)					
Output Voltage ($I_O = 0 \text{ mA}, T_J = 25^{\circ}\text{C}$)	V _{reg}	5.5	6.5	7.5	V
Line Regulation (V _{CC} = 20 V to 40 V)	Reg _{line}	-	30	500	mV
Load Regulation (I _O = 0 mA to 10 mA)	Reg _{load}	-	44	200	mV
Total Output Variation over Line, Load, and Temperature	V _{reg}	5.3	-	8.0	V
OSCILLATOR (Pin 7)	•			•	
Frequency $C_T = 390 \text{ pF}$ $T_J = 25^{\circ}\text{C (V}_{CC} = 20 \text{ V)}$ $T_J = T_{low} \text{ to } T_{high} \text{ (V}_{CC} = 20 \text{ V to } 40 \text{ V)}$ $C_T = 2.0 \text{ nF}$ $T_J = 25^{\circ}\text{C (V}_{CC} = 20 \text{ V)}$ $T_J = T_{low} \text{ to } T_{high} \text{ (V}_{CC} = 20 \text{ V to } 40 \text{ V)}$	fosc	260 255 60 59	285 - 67.5	310 315 75 76	kHz
Frequency Change with Voltage (V _{CC} = 20 V to 40 V)	Δfosc/ΔV	_	0.1	2.0	kHz

^{1.} This device series contains ESD protection and exceeds the following tests: Human Body Model 2000 V per MIL–STD–883, Method 3015. Machine Model Method 200 V.

Maximum power dissipation limits must be observed.
 Tested junction temperature range for the MC33362:

 $T_{low} = -25^{\circ}C$ $T_{high} = +125^{\circ}C$

ELECTRICAL CHARACTERISTICS (V_{CC} = 20 V, R_T = 10 k, C_T = 390 pF, $C_{Pin~8}$ = 1.0 μ F, for typical values T_J = 25°C, for min/max values T_J is the operating junction temperature range that applies (Note 4), unless otherwise noted.)

Characteristic	Symbol	Min	Тур	Max	Unit
ERROR AMPLIFIER (Pins 9, 10)					
Voltage Feedback Input Threshold	V_{FB}	2.52	2.6	2.68	V
Line Regulation (V _{CC} = 20 V to 40 V, T _J = 25°C)	Reg _{line}	-	0.6	5.0	mV
Input Bias Current (V _{FB} = 2.6 V)	I _{IB}	-	20	500	nA
Open Loop Voltage Gain (T _J = 25°C)	A _{VOL}	_	82	_	dB
Gain Bandwidth Product (f = 100 kHz, T _J = 25°C)	GBW	_	1.0	_	MHz
Output Voltage Swing High State (I_{Source} = 100 μ A, V_{FB} < 2.0 V) Low State (I_{Sink} = 100 μ A, V_{FB} > 3.0 V)	V _{OH} V _{OL}	4.0 _	5.3 0.2	_ 0.35	V
OVERVOLTAGE DETECTION (Pin 11)					
Input Threshold Voltage	V _{th}	2.47	2.6	2.73	V
Input Bias Current (V _{in} = 2.6 V)	I _{IB}	-	100	500	nA
PWM COMPARATOR (Pins 7, 9)					
Duty Cycle Maximum (V _{FB} = 0 V) Minimum (V _{FB} = 2.7 V)	DC _(max) DC _(min)	48 -	50 0	52 0	%
POWER SWITCH (Pin 16)		•	<u> </u>	·	1
Drain–Source On–State Resistance (I_D = 200 mA) T_J = 25°C T_J = T_{low} to T_{high}	R _{DS(on)}	_ _	4.4 _	6.0 12	Ω
Drain-Source Off-State Leakage Current (V _{DS} = 500 V)	I _{D(off)}	-	0.2	50	μΑ
Rise Time	t _r	-	50	_	ns
Fall Time	t _f	-	50	_	ns
OVERCURRENT COMPARATOR (Pin 16)		•	1	1	•
Current Limit Threshold (R _T = 10 k)	I _{lim}	0.7	0.9	1.1	Α
STARTUP CONTROL (Pin 1)		•			
Peak Startup Current ($V_{in} = 200 \text{ V}$) $V_{CC} = 0 \text{ V}$ $V_{CC} = (V_{th(on)} - 0.2 \text{ V})$	I _{start}	_ _	55 26	_ _	mA
Off–State Leakage Current (V _{in} = 50 V, V _{CC} = 20 V)	I _{D(off)}	-	40	200	μΑ
UNDERVOLTAGE LOCKOUT (Pin 3)	<u>,</u>	•	•	•	
Startup Threshold (V _{CC} Increasing)	V _{th(on)}	11	14.5	18	V
Minimum Operating Voltage After Turn-On	V _{CC(min)}	7.5	9.5	11.5	V
TOTAL DEVICE (Pin 3)		- 			
Power Supply Current Startup (V _{CC} = 10 V, Pin 1 Open) Operating	Icc	_ _	0.3 3.6	0.5 5.0	mA

^{4.} Tested junction temperature range for the MC33362: $T_{low} = -25^{\circ}C \qquad T_{high} = +125^{\circ}C$

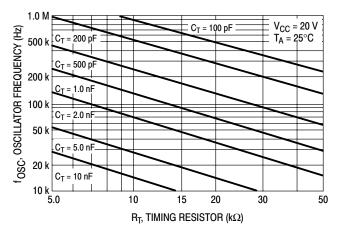


Figure 2. Oscillator Frequency versus Timing Resistor

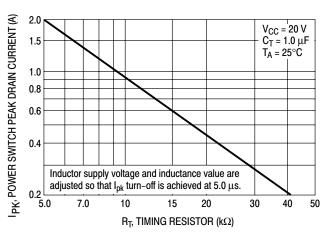


Figure 3. Power Switch Peak Drain Current versus Timing Resistor

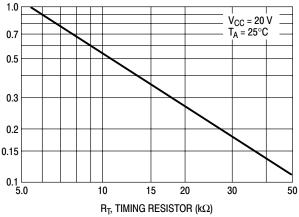


Figure 4. Oscillator Charge/Discharge Current versus Timing Resistor

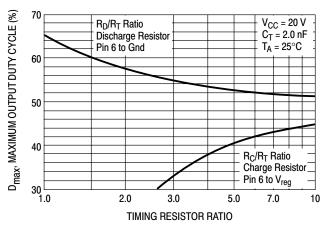


Figure 5. Maximum Output Duty Cycle versus Timing Resistor Ratio

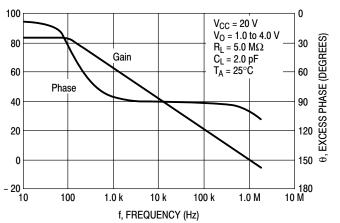


Figure 6. Error Amp Open Loop Gain and Phase versus Frequency

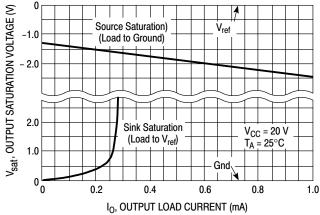


Figure 7. Error Amp Output Saturation Voltage versus Load Current

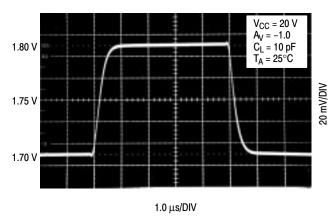


Figure 8. Error Amplifier Small Signal Transient Response

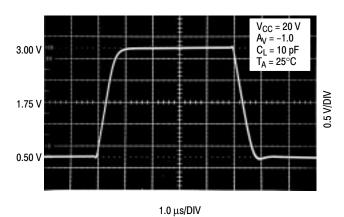


Figure 9. Error Amplifier Large Signal Transient Response

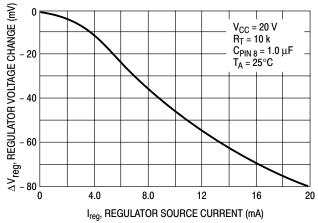


Figure 10. Regulator Output Voltage Change versus Source Current

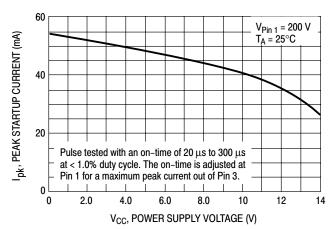


Figure 11. Peak Startup Current versus Power Supply Voltage

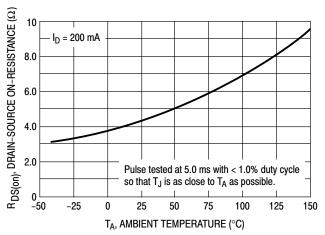


Figure 12. Power Switch Drain-Source On-Resistance versus Temperature

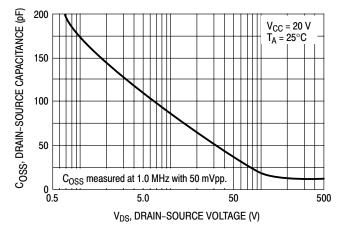


Figure 13. Power Switch
Drain-Source Capacitance versus Voltage

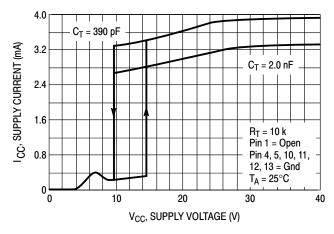


Figure 14. Supply Current versus Supply Voltage

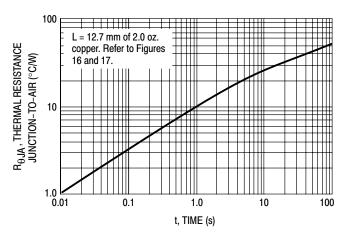


Figure 15. DW and P Suffix Transient Thermal Resistance

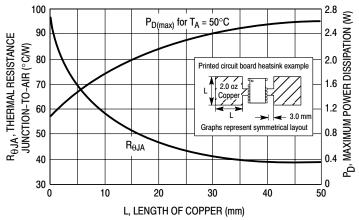


Figure 16. DW Suffix (SOP-16L) Thermal Resistance and Maximum Power Dissipation versus P.C.B. Copper Length

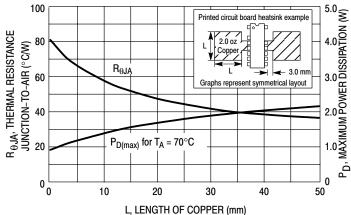


Figure 17. P Suffix (DIP-16) Thermal Resistance and Maximum Power Dissipation versus P.C.B. Copper Length

PIN FUNCTION DESCRIPTION

Pin	Function	Description
1	Startup Input	This pin connects directly to the rectified ac line voltage source. Internally Pin 1 is tied to the drain of a high voltage startup MOSFET. During startup, the MOSFET supplies internal bias, and charges an external capacitor that connects from the V _{CC} pin to ground.
2	-	This pin has been omitted for increased spacing between the rectified AC line voltage on Pin 1 and the $V_{\rm CC}$ potential on Pin 3.
3	V _{CC}	This is the positive supply voltage input. During startup, power is supplied to this input from Pin 1. When V_{CC} reaches the UVLO upper threshold, the startup MOSFET turns off and power is supplied from an auxiliary transformer winding.
4, 5, 12, 13	Ground	These pins are the control circuit grounds. They are part of the IC lead frame and provide a thermal path from the die to the printed circuit board.
6	R _T	Resistor R_T connects from this pin to ground. The value selected will program the Current Limit Comparator threshold and affect the Oscillator frequency.
7	Ст	Capacitor C_T connects from this pin to ground. The value selected, in conjunction with resistor R_T , programs the Oscillator frequency.
8	Regulator Output	This 6.5 V output is available for biasing external circuitry. It requires an external bypass capacitor of at least 1.0 µF for stability.
9	Compensation	This pin is the Error Amplifier output and is made available for loop compensation. It can be used as an input to directly control the PWM Comparator.
10	Voltage Feedback Input	This is the inverting input of the Error Amplifier. It has a 2.6 V threshold and normally connects through a resistor divider to the converter output, or to a voltage that represents the converter output.
11	Overvoltage Protection Input	This input provides runaway output voltage protection due to an external component or connection failure in the control loop feedback signal path. It has a 2.6 V threshold and normally connects through a resistor divider to the converter output, or to a voltage that represents the converter output.
14, 15	_	These pins have been omitted for increased spacing between the high voltages present on the Power Switch Drain, and the ground potential on Pins 12 and 13.
16	Power Switch Drain	This pin is designed to directly drive the converter transformer and is capable of switching a maximum of 500 V and 2.0 A.

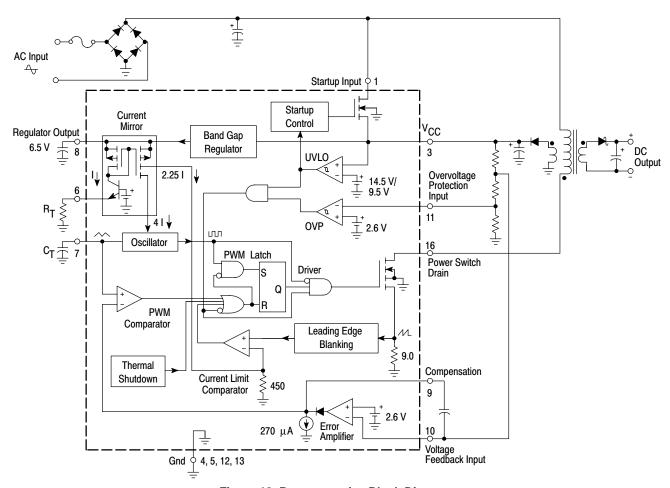


Figure 18. Representative Block Diagram

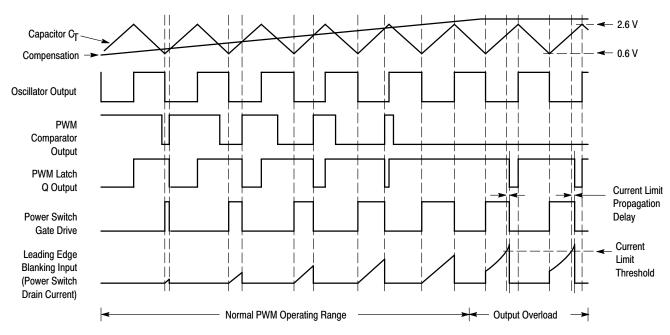


Figure 19. Timing Diagram

OPERATING DESCRIPTION

Introduction

The MC33362 represents a new higher level of integration by providing all the active high voltage power, control, and protection circuitry required for implementation of a flyback or forward converter on a single monolithic chip. This device is designed for direct operation from a rectified 120 VAC line source and requires a minimum number of external components to implement a complete converter. A description of each of the functional blocks is given below, and the representative block and timing diagrams are shown in Figures 18 and 19.

Oscillator and Current Mirror

The oscillator frequency is controlled by the values selected for the timing components R_T and C_T. Resistor R_T programs the oscillator charge/discharge current via the Current Mirror 4 I output, Figure 4. Capacitor C_T is charged and discharged by an equal magnitude internal current source and sink. This generates a symmetrical 50 percent duty cycle waveform at Pin 7, with a peak and valley threshold of 2.6 V and 0.6 V respectively. During the discharge of C_T, the oscillator generates an internal blanking pulse that holds the inverting input of the AND gate Driver high. This causes the Power Switch gate drive to be held in a low state, thus producing a well controlled amount of output deadtime. The amount of deadtime is relatively constant with respect to the oscillator frequency when operating below 1.0 MHz. The maximum Power Switch duty cycle at Pin 16 can be modified from the internal 50% limit by providing an additional charge or discharge current path to C_T, Figure 20. In order to increase the maximum duty cycle, a discharge current resistor R_D is connected from Pin 7 to ground. To decrease the maximum duty cycle, a charge current resistor R_C is connected from Pin 7 to the Regulator Output. Figure 5 shows an obtainable range of maximum output duty cycle versus the ratio of either R_C or R_D with respect to R_T .

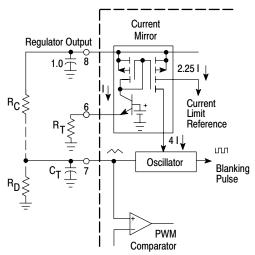


Figure 20. Maximum Duty Cycle Modification

The formula for the charge/discharge current along with the oscillator frequency are given below. The frequency formula is a first order approximation and is accurate for C_T values greater than 500 pF. For smaller values of C_T , refer to Figure 2. Note that resistor R_T also programs the Current Limit Comparator threshold.

$$I_{chg/dscg} = \frac{5.4}{R_T}$$
 $f \approx \frac{I_{chg/dscg}}{4C_T}$

PWM Comparator and Latch

The pulse width modulator consists of a comparator with the oscillator ramp voltage applied to the non–inverting input, while the error amplifier output is applied into the inverting input. The Oscillator applies a set pulse to the PWM Latch while C_T is discharging, and upon reaching the valley voltage, Power Switch conduction is initiated. When C_T charges to a voltage that exceeds the error amplifier output, the PWM Latch is reset, thus terminating Power Switch conduction for the duration of the oscillator ramp—up period. This PWM Comparator/Latch combination prevents multiple output pulses during a given oscillator clock cycle. The timing diagram shown in Figure 19 illustrates the Power Switch duty cycle behavior versus the Compensation voltage.

Current Limit Comparator and Power Switch

The MC33362 uses cycle—by—cycle current limiting as a means of protecting the output switch transistor from overstress. Each on—cycle is treated as a separate situation. Current limiting is implemented by monitoring the output switch current buildup during conduction, and upon sensing an overcurrent condition, immediately turning off the switch for the duration of the oscillator ramp—up period.

The Power Switch is constructed as a SENSEFET allowing a virtually lossless method of monitoring the drain current. It consists of a total of 3770 cells, of which 50 are connected to a 9.0 Ω ground-referenced sense resistor. The Current Sense Comparator detects if the voltage across the sense resistor exceeds the reference level that is present at the inverting input. If exceeded, the comparator quickly resets the PWM Latch, thus protecting the Power Switch. The current limit reference level is generated by the 2.25 I output of the Current Mirror. This current causes a reference voltage to appear across the 450 Ω resistor. This voltage level, as well as the Oscillator charge/discharge current are both set by resistor R_T. Therefore when selecting the values for R_T and C_T , R_T must be chosen first to set the Power Switch peak drain current, while C_T is chosen second to set the desired Oscillator frequency. A graph of the Power Switch peak drain current versus R_T is shown in Figure 3 with the related formula below.

$$I_{pk} = 12.3 \left(\frac{R_T}{1000}\right) - 1.115$$

The Power Switch is designed to directly drive the converter transformer and is capable of switching a maximum of 500 V and 2.0 A. Proper device voltage snubbing and heatsinking are required for reliable operation.

A Leading Edge Blanking circuit was placed in the current sensing signal path. This circuit prevents a premature reset of the PWM Latch. The premature reset is generated each time the Power Switch is driven into conduction. It appears as a narrow voltage spike across the current sense resistor, and is due to the MOSFET gate to source capacitance, transformer interwinding capacitance, and output rectifier recovery time. The Leading Edge Blanking circuit has a dynamic behavior in that it masks the current signal until the Power Switch turn—on transition is completed. The current limit propagation delay time is typically 233 ns. This time is measured from when an overcurrent appears at the Power Switch drain, to the beginning of turn—off.

Error Amplifier

An fully compensated Error Amplifier with access to the inverting input and output is provided for primary side voltage sensing, Figure 18. It features a typical dc voltage gain of 82 dB, and a unity gain bandwidth of 1.0 MHz with 78 degrees of phase margin, Figure 6. The noninverting input is internally biased at 2.6 V ±3.1% and is not pinned out. The Error Amplifier output is pinned out for external loop compensation and as a means for directly driving the PWM Comparator. The output was designed with a limited sink current capability of 270 µA, allowing it to be easily overridden with a pull-up resistor. This is desirable in applications that require secondary side voltage sensing, Figure 21. In this application, the Voltage Feedback Input is connected to the Regulator Output. This disables the Error Amplifier by placing its output into the sink state, allowing the optocoupler transistor to directly control the PWM Comparator.

Overvoltage Protection

An Overvoltage Protection Comparator is included to eliminate the possibility of runaway output voltage. This condition can occur if the control loop feedback signal path is broken due to an external component or connection failure. The comparator is normally used to monitor the primary side $V_{\rm CC}$ voltage. When the 2.6 V threshold is exceeded, it will immediately turn off the Power Switch, and protect the load from a severe overvoltage condition. This input can also be driven from external circuitry to inhibit converter operation.

Undervoltage Lockout

An Undervoltage Lockout comparator has been incorporated to guarantee that the integrated circuit has sufficient voltage to be fully functional before the output stage is enabled. The UVLO comparator monitors the $V_{\rm CC}$ voltage at Pin 3 and when it exceeds 14.5 V, the reset signal is removed from the PWM Latch allowing operation of the

Power Switch. To prevent erratic switching as the threshold is crossed, 5.0 V of hysteresis is provided.

Startup Control

An internal Startup Control circuit with a high voltage enhancement mode MOSFET is included within the MC33362. This circuitry allows for increased converter efficiency by eliminating the external startup resistor, and its associated power dissipation, commonly used in most off–line converters that utilize a UC3842 type of controller. Rectified ac line voltage is applied to the Startup Input, Pin 1. This causes the MOSFET to enhance and supply internal bias as well as charge current to the V_{CC} bypass capacitor that connects from Pin 3 to ground. When V_{CC} reaches the UVLO upper threshold of 14.5 V, the IC commences operation and the startup MOSFET is turned off. Operating bias is now derived from the auxiliary transformer winding, and all of the device power is efficiently converted down from the rectified ac line.

The startup MOSFET will provide an initial peak current of 55 mA, Figure 11, which decreases rapidly as $V_{\rm CC}$ and the die temperature rise. The steady state current will self limit in the range of 12 mA with V_{CC} shorted to ground. The startup MOSFET is rated at a maximum of 250 V with $V_{\rm CC}$ shorted to ground, and 400 V when charging a $V_{\rm CC}$ capacitor of 1000 μF or less.

Regulator

A low current 6.5 V regulated output is available for biasing the Error Amplifier and any additional control system circuitry. It is capable of up to 10 mA and has short–circuit protection. This output requires an external bypass capacitor of at least 1.0 μF for stability.

Thermal Shutdown and Package

Internal thermal circuitry is provided to protect the Power Switch in the event that the maximum junction temperature is exceeded. When activated, typically at 155°C, the Latch is forced into a 'reset' state, disabling the Power Switch. The Latch is allowed to 'set' when the Power Switch temperature falls below 145°C. This feature is provided to prevent catastrophic failures from accidental device overheating. It is not intended to be used as a substitute for proper heatsinking.

The MC33362 is contained in a heatsinkable plastic dual—in—line package in which the die is mounted on a special heat tab copper alloy lead frame. This tab consists of the four center ground pins that are specifically designed to improve thermal conduction from the die to the circuit board. Figures 16 and 17 show a simple and effective method of utilizing the printed circuit board medium as a heat dissipater by soldering these pins to an adequate area of copper foil. This permits the use of standard layout and mounting practices while having the ability to halve the junction to air thermal resistance. The examples are for a symmetrical layout on a single—sided board with two ounce per square foot of copper. Figure 23 shows a practical example of a printed circuit board layout

that utilizes the copper foil as a heat dissipater. Note that a jumper was added to the layout from Pins 8 to 10 in order to enhance the copper area near the device for improved thermal

conductivity. The application circuit requires two ounce copper foil in order to obtain 20 watts of continuous output power at room temperature.

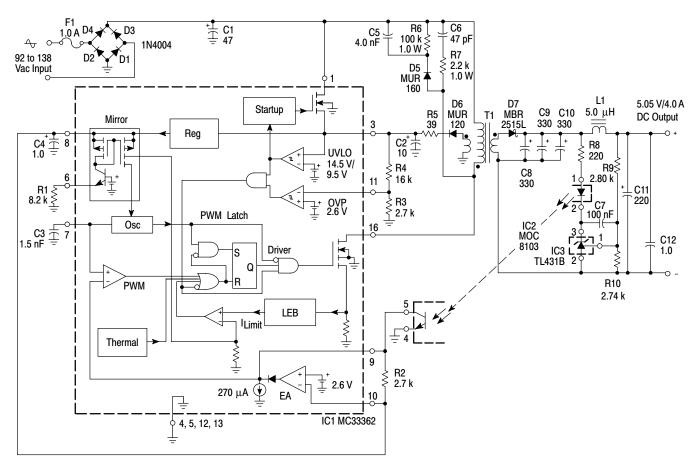


Figure 21. 20 W Off-Line Converter

Test	Conditions	Results
Line Regulation	V _{in} = 92 Vac to 138 Vac, I _O 4.0 A	Δ = 1.0 mV
Load Regulation	V _{in} = 115 Vac, I _O = 1.0 A to 4.0 A	Δ = 9.0 mV
Output Ripple	V _{in} = 115 Vac, I _O = 4.0 A	Triangular = 10 mVpp Spike = 60 mVpp
Efficiency	V _{in} = 115 Vac, I _O = 4.0 A	78.4%

This data was taken with the components listed below mounted on the printed circuit board shown in Figure 23. For high efficiency and small circuit board size, the Sanyo Os-Con capacitors are recommended for C8, Č9, C10 and C11. C8, C9, C10 = Sanyo Os-Con #6SA330M, 330 μF 6.3 V.

C11 = Sanyo Os-Con #10SA220M, 220 µF 10 V.

D7 = MBR2515L mounted on Aavid #592502B03400 heatsink.

L1 = Coilcraft S5088–A, 5.0 μ H, 0.11 Ω .

T1 = Coilcraft S5069-A

Primary: 58 turns of # 26 AWG, Pin 1 = start, Pin 8 = finish.

Two layers 0.002" Mylar tape.

Secondary: 4 turns of # 18 AWG, 2 strands bifiliar wound, Pin 5 = start, Pin 4 = finish.

Two layers 0.002" Mylar tape

Auxiliary: 10 turns of # 26 AWG wound in center of bobbin, Pin 2 = start, Pin 7 = finish.

Two layers 0.002" Mylar tape.

Gap: 0.014" total for a primary inductance (LP) of 330 μH.

Core and Bobbin: Coilcraft PT1950, E187, 3F3 material.

Figure 22. Converter Test Data

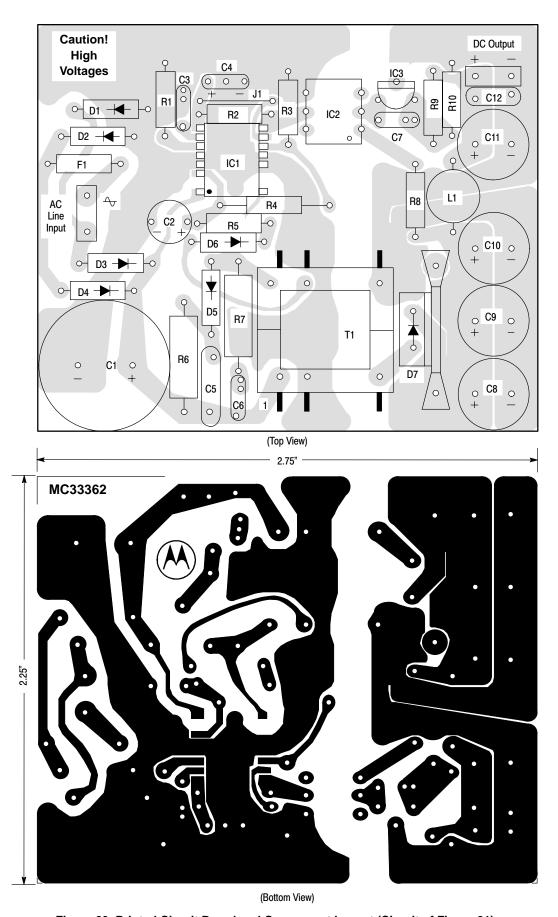
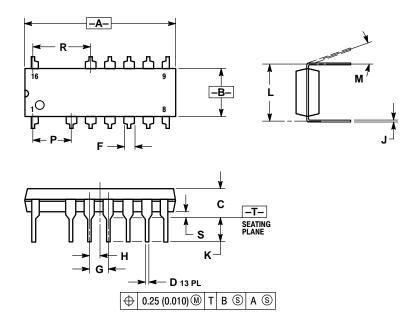


Figure 23. Printed Circuit Board and Component Layout (Circuit of Figure 21)

PACKAGE DIMENSIONS

PDIP-16 **P SUFFIX** CASE 648E-01 **ISSUE O**



NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

- Y14.5M, 1982.

 2. CONTROLLING DIMENSION: INCH.

 3. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.

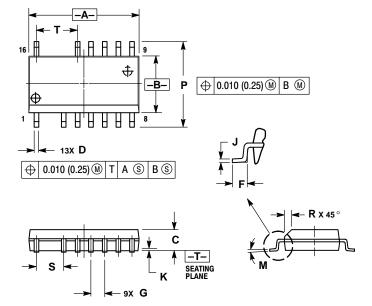
 4. DIMENSION A AND B DOES NOT INCLUDE MOLD PROTRUSION.

 5. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.25 (0.010).

 6. ROUNDED CORNER OPTIONAL.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.740	0.760	18.80	19.30
В	0.245	0.260	6.23	6.60
С	0.145	0.175	3.69	4.44
D	0.015	0.021	0.39	0.53
F	0.050	0.070	1.27	1.77
G	0.100 BSC		2.54 BSC	
Н	0.050	BSC	1.27 BSC	
_	0.008	0.015	0.21	0.38
K	0.120	0.140	3.05	3.55
L	0.295	0.305	7.50	7.74
M	0 °	10°	0 °	10°
P	0.200 BSC		5.08 BSC	
R	0.300 BSC		7.62 BSC	
S	0.015	0.035	0.39	0.88

SO-16W **DW SUFFIX** CASE 751N-01 **ISSUE O**



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
- 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
- SIDE.

 5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.13 (0.005) TOTAL IN EXCESS OF D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIN	IETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	10.15	10.45	0.400	0.411	
В	7.40	7.60	0.292	0.299	
С	2.35	2.65	0.093	0.104	
D	0.35	0.49	0.014	0.019	
F	0.50	0.90	0.020	0.035	
G	1.27	BSC	0.050 BSC		
J	0.25	0.32	0.010	0.012	
K	0.10	0.25	0.004	0.009	
M	0 °	7 °	0 °	7°	
P	10.05	10.55	0.395	0.415	
R	0.25	0.75	0.010	0.029	
S	2.54 BSC		0.100	BSC	
T	3.81 BSC		0.150	BSC	

Notes

Notes

The product described herein (MC33362), may be covered by one or more of the following U.S. patents: 4,553,084; 5,418,410; 5,477,175. There may be other patents pending.

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